

Description

The DMN2025U-13 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

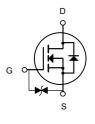
D S S S S SOT-23

General Features

 $V_{DS} = 20V I_{D} = 6A$

 $R_{DS(ON)}$ < 17m Ω @ V_{GS}=4. 5V

ESD=2500V HBM



Application

Battery protection

Load switch

Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMN2025U-13	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 [°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	20	V
V _G s	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	6	Α
Ідм	Drain Current-Pulsed (Note 1)	30	Α
P _D	Maximum Power Dissipation	1.4	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	89	°C/W



Electrical Characteristics (T_A=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20		-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V_{GS} =±10 V , V_{DS} =0 V	-	-	±10	μA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.45	0.7	1.0	V
		V _{GS} =4.5V, I _D =6.5A	-	14	17	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =2.5V, I _D =5.5A	-	18	23	mΩ
		V _{GS} =1.8V, I _D =5A	-	28	40	mΩ
Forward Transconductance	grs	V_{DS} =5 V , I_{D} =6.5 A	8	-	-	S
Input Capacitance	Clss		-	660	-	PF
Output Capacitance	Coss	V_{DS} =10V, V_{GS} =0V, F=1.0MHz	-	160	-	PF
Reverse Transfer Capacitance	Crss	1 - 1.0Wii 12	-	87	-	PF
Turn-on Delay Time	td(on)		-	0.5		nS
Turn-on Rise Time	tr	V _{DD} =10V,R _L =1. 5Ω	-	1		nS
Turn-Off Delay Time	td(off)	$V_{\text{GS}}\text{=}5\text{V}, R_{\text{GEN}}\text{=}3\Omega$	-	12		nS
Turn-Off Fall Time	t _f		-	4		nS
Total Gate Charge	Qg		-	8		nC
Gate-Source Charge	Qgs	Q _{gs} V _{DS} =10V,I _D =6.5A, V _{GS} =4.5V	-	2.5	-	nC
Gate-Drain Charge	Q_{gd}	v GS-4.0 v	-	3	-	nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =6.5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6.0	Α

Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board, $t \leq 10$ sec. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. Guaranteed by design, not subject to production



Typical Characteristics

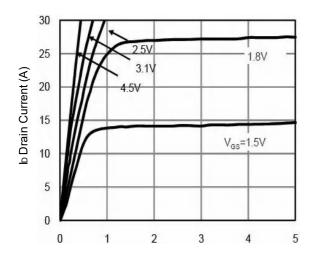


Fig.1 Typical Output Characteristics

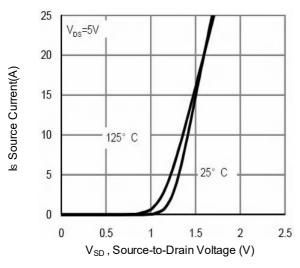


Fig.3 Forward Characteristics of Reverse

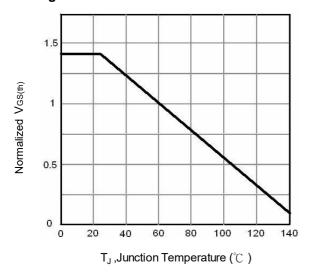


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

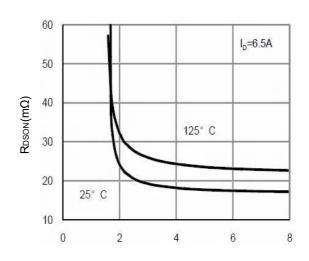


Fig.2 On-Resistance vs. Gate-Source

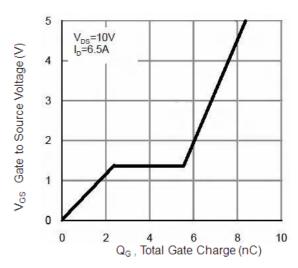


Fig.4 Gate-Charge Characteristics

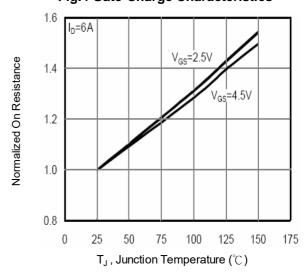
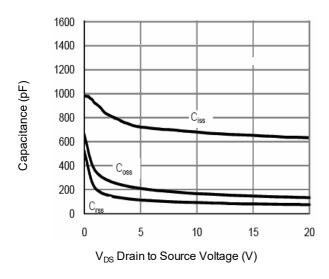


Fig.6 Normalized R_{DSON} vs. T_J





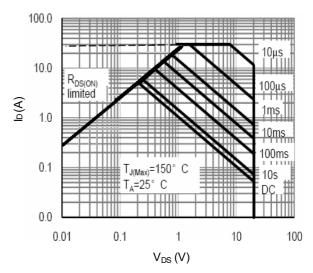
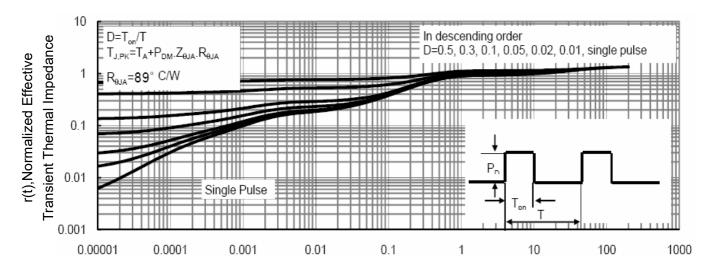


Fig.7 Capacitance

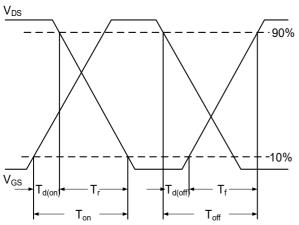
Fig.8 Safe Operating Area

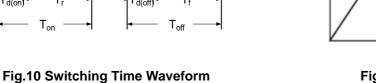


Square Wave Pluse Duration(sec)
Fig.9 Normalized Maximum Transient Thermal Impedance

4.5\

Qgs





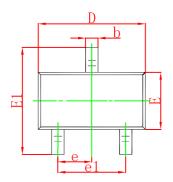
Charge Fig.11 Gate Charge Waveform

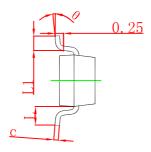
Qg

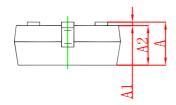
Qgd



SOT-23 Package Outline Dimensions

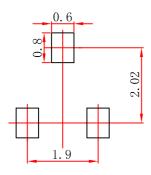






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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